

Phase Control Thyristors (Stud Version), 180 A



TO-209AB (TO-93)

FEATURES

- Hermetic glass-metal seal
- International standard case TO-209AB (TO-93)
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

PRODUCT SUMMARY

$I_{T(AV)}$	180 A
V_{DRM}/V_{RRM}	400 V, 800 V, 1000 V
V_{TM}	1.35 V
I_{GT}	65 mA
T_J	-40 °C to 125 °C
Package	TO-209AB (TO-93)
Diode variation	Single SCR

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		180	A
	T_C	80	°C
$I_{T(RMS)}$		285	A
I_{TSM}	50 Hz	3800	
	60 Hz	4000	
I^2t	50 Hz	72	kA ² s
	60 Hz	66	
V_{DRM}/V_{RRM}		400 to 1000	V
t_q	Typical	100	μs
T_J		-40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

PART NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-180RKI VS-181RKI	40	400	500	30
	80	800	900	
	100	1000	1100	



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at case temperature	I _{T(AV)}	180° conduction, half sine wave			180	A
					80	°C
Maximum RMS on-state current	I _{RMS}	DC at 79 °C case temperature			285	A
Maximum peak, one-cycle non-repetitive surge current	I _{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T _J = T _J maximum	3800	
		t = 8.3 ms			4000	
		t = 10 ms	100 % V _{RRM} reapplied		3500	
		t = 8.3 ms			3660	
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied		72	kA ² s
		t = 8.3 ms			66	
		t = 10 ms	100 % V _{RRM} reapplied		61	
		t = 8.3 ms			56	
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to 10 ms, no voltage reapplied			720	kA ² √s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)} , T _J = T _J maximum			0.83	V
High level value of threshold voltage	V _{T(TO)2}	(I > π × I _{T(AV)}), T _J = T _J maximum			0.89	
Low level value of on-state slope resistance	r _{t1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)} , T _J = T _J maximum			0.92	mΩ
High level value of on-state slope resistance	r _{t2}	(I > π × I _{T(AV)}), T _J = T _J maximum			0.81	
Maximum on-state voltage	V _{TM}	I _{pk} = 570 A, T _J = T _J maximum, t _p = 10 ms sine pulse			1.35	V
Maximum holding current	I _H	T _J = 25 °C, anode supply 12 V resistive load			600	mA
Typical latching current	I _L				1000	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	di/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1$ μs $T_J = T_J$ maximum, anode voltage ≤ 80 % V_{DRM}	300	A/μs
Typical delay time	t_d	Gate current 1 A, $di_g/dt = 1$ A/μs $V_d = 0.67$ % V_{DRM} , $T_J = 25$ °C	1.0	μs
Typical turn-off time	t_q	$I_{TM} = 50$ A, $T_J = T_J$ maximum, $di/dt = 10$ A/μs, $V_R = 100$ V, $dV/dt = 20$ V/μs	100	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/μs
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM}	$T_J = T_J$ maximum rated V_{DRM}/V_{RRM} applied	30	mA



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
				TYP.	MAX.	
Maximum peak gate power	P _{GM}	T _J = T _J maximum, t _p ≤ 5 ms		10		W
Maximum average gate power	P _{G(AV)}	T _J = T _J maximum, f = 50 Hz, d% = 50		2.0		
Maximum peak positive gate current	I _{GM}	T _J = T _J maximum, t _p ≤ 5 ms		3.0		A
Maximum peak positive gate voltage	+ V _{GM}			20		V
Maximum peak negative gate voltage	- V _{GM}			5.0		
DC gate current required to trigger	I _{GT}	T _J = - 40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	130	-	mA
		T _J = 25 °C		65	150	
		T _J = 125 °C		35	-	
DC gate voltage required to trigger	V _{GT}	T _J = - 40 °C		2.0	-	V
		T _J = 25 °C		1.2	2.5	
		T _J = 125 °C		0.9	-	
DC gate current not to trigger	I _{GD}	T _J = T _J maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	10		mA
DC gate voltage not to trigger	V _{GD}			0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum operating junction temperature range	T_J			-40 to 125	°C
Maximum storage temperature range	T_{Stg}			-40 to 150	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation		0.15	K/W
Maximum thermal resistance, junction to ambient	R_{thCS}	Mounting surface, smooth, flat and greased		0.04	
Mounting force, ± 10 %		Non-lubricated threads		31 (275)	N · m (lbf · in)
		Lubricated threads		24.5 (210)	
Approximate weight				280	g
Case style		See dimensions - link at the end of datasheet		TO-209AB (TO-93)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.050	0.032	$T_J = T_J$ maximum	K/W
120°	0.063	0.059		
90°	0.080	0.082		
60°	0.118	0.124		
30°	0.225	0.228		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

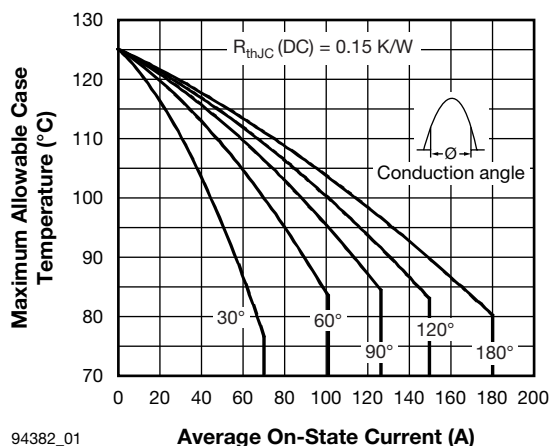


Fig. 1 - Current Ratings Characteristics

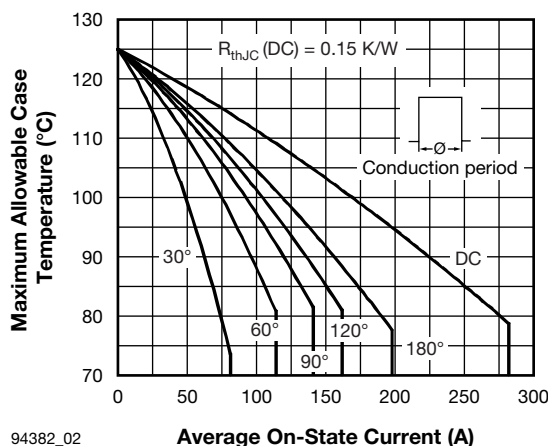


Fig. 2 - Current Ratings Characteristics

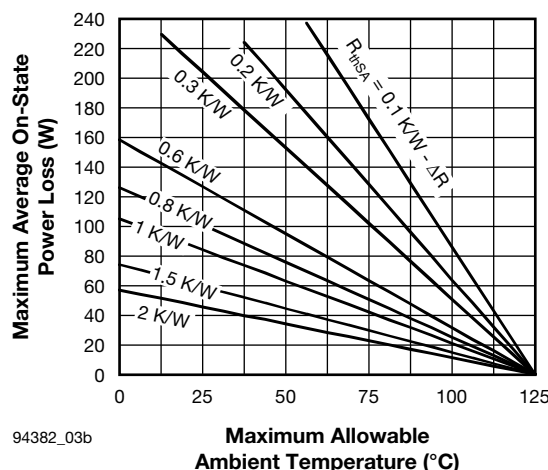
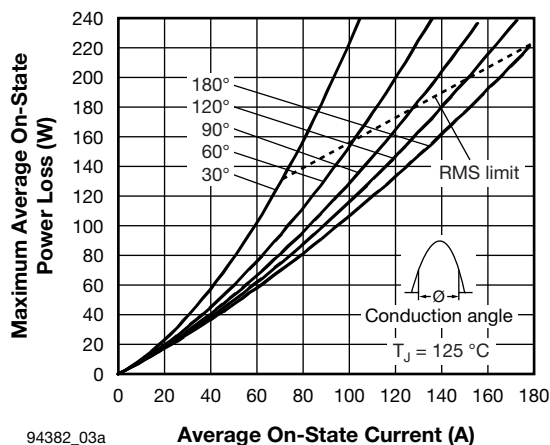


Fig. 3 - On-State Power Loss Characteristics

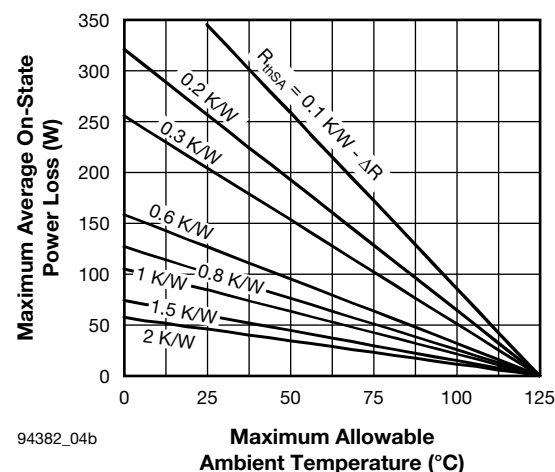
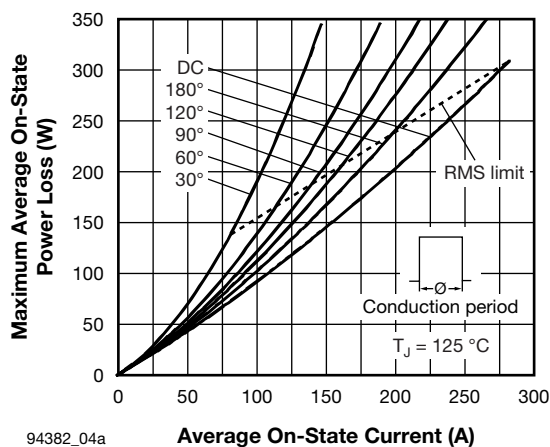


Fig. 4 - On-State Power Loss Characteristics

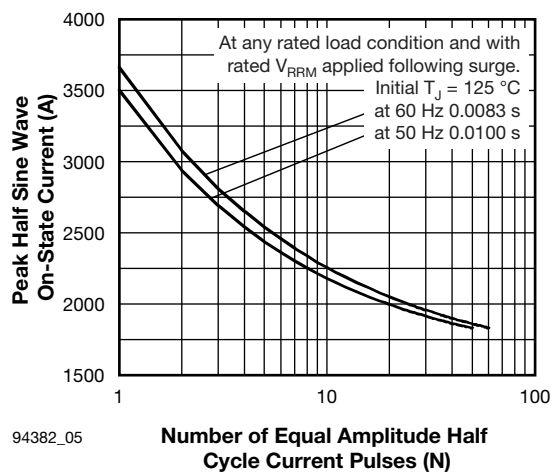


Fig. 5 - Maximum Non-Repetitive Surge Current

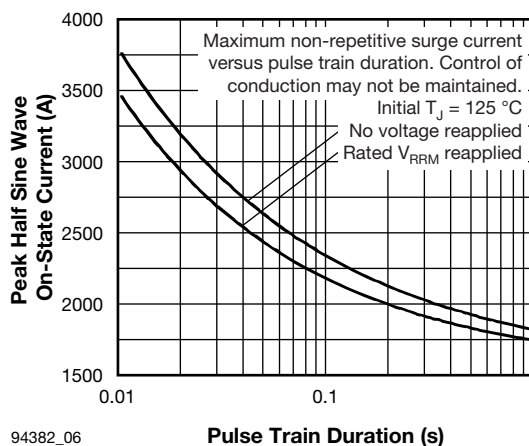


Fig. 6 - Maximum Non-Repetitive Surge Current

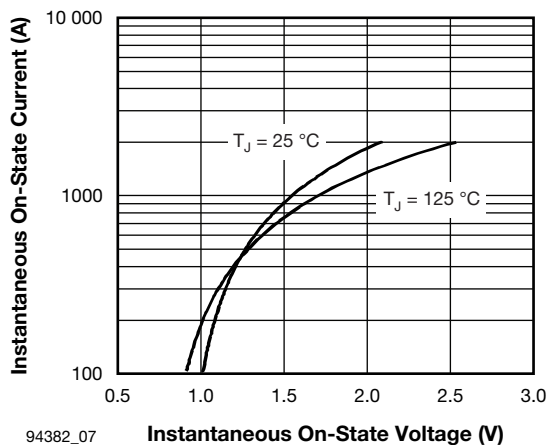


Fig. 7 - On-State Voltage Drop Characteristics

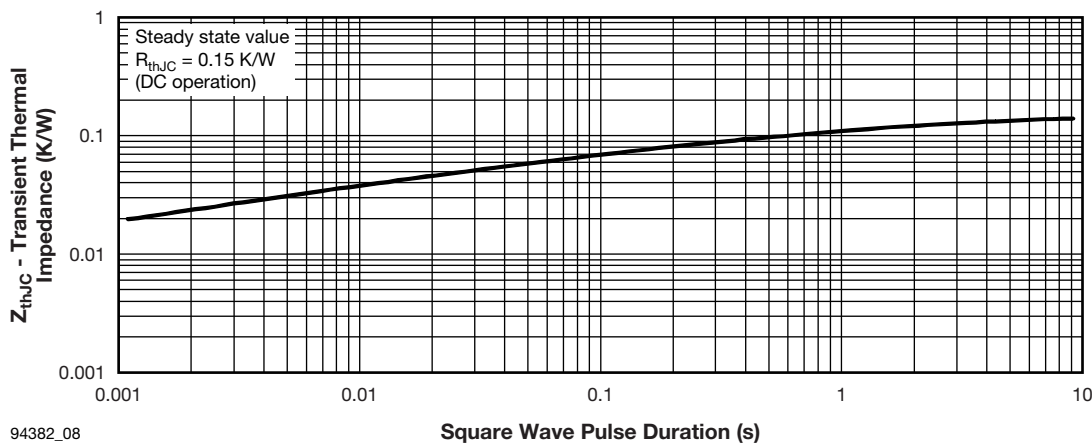


Fig. 8 - Thermal impedance Z_{thJC} Characteristics

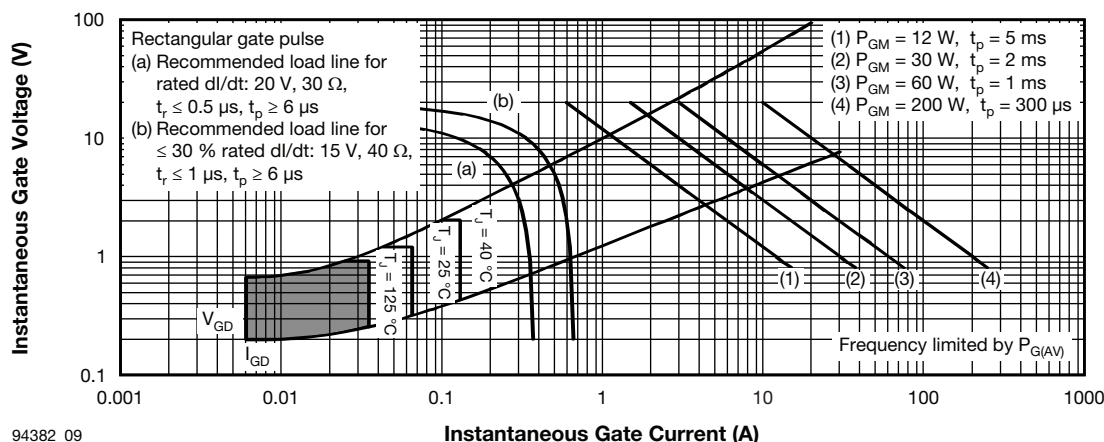


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	18	1	RKI	100	PbF
	1	2	3	4	5	6
1	- Vishay Semiconductors product					
2	- $I_{T(AV)}$ rated average output current (rounded/10)					
3	0 = Eyelet terminals (gate and auxiliary cathode leads) 1 = Fast-on terminals (gate and auxiliary cathode leads)					
4	- Thyristor					
5	- Voltage code x 10 = V_{RRM} (see Voltage Ratings table)					
6	- None = Standard production - PbF = Lead (Pb)-free					

LINKS TO RELATED DOCUMENTS

Dimensions

www.vishay.com/doc?95077

DIMENSIONS in millimeters (inches)





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